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1. Global joint venture starts operations as WeEn Semiconductors

Dear customer.

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





1. General description

Planar passivated Silicon Controlled Rectifier with sensitive gate in a SOT54 (TO-92) plastic package. This SCR is designed to be interfaced directly to microcontrollers, logic ICs and other low power gate trigger circuits.

2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Direct triggering from low power gate circuits and logic ICs

3. Applications

- · Ignition circuits
- Lighting ballasts
- Protection circuits
- Switched Mode Power Supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	400	V
V_{RRM}	repetitive peak reverse voltage		-	-	400	V
I _{TSM} non-repetitive peak state current	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	-	8	Α
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms	-	-	9	А
T _j	junction temperature		-	-	125	°C
I _{T(AV)}	average on-state current	half sine wave; T _{lead} ≤ 83 °C; <u>Fig. 1</u>	-	-	0.5	А
I _{T(RMS)}	RMS on-state current	half sine wave; T _{lead} ≤ 83 °C; <u>Fig. 2;</u> <u>Fig. 3</u>	-	-	0.8	А
Static charact	eristics					
I _{GT}	gate trigger current	V_D = 12 V; I_T = 10 mA; T_j = 25 °C; Fig. 7	-	50	200	μA
Dynamic char	acteristics					,

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 268 V; T_j = 125 °C; R_{GK} = 1 kΩ; exponential waveform; Fig. 12	500	800	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Α	anode		А - [] К
2	G	gate		G sym037
3	К	cathode		- Syllius/
			TO-92 (SOT54)	

6. Ordering information

Table 3. Ordering information

Type number	Package	ackage				
	Name	Description	Version			
BT169D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

7. Marking

Table 4. Marking codes

Type number	Marking code
BT169D	BT169DH

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	400	V
V_{RRM}	repetitive peak reverse voltage		-	400	V
I _{T(AV)}	average on-state current	half sine wave; T _{lead} ≤ 83 °C; <u>Fig. 1</u>	-	0.5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{lead} ≤ 83 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	0.8	Α
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	8	А
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms	-	9	Α

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Symbol	Parameter	Conditions	Min	Max	Unit
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.32	A²s
dl _T /dt	rate of rise of on-state current	$I_T = 2 \text{ A}$; $I_G = 10 \text{ mA}$; $dI_G/dt = 100 \text{ mA/}\mu\text{s}$	-	50	A/µs
I _{GM}	peak gate current		-	1	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

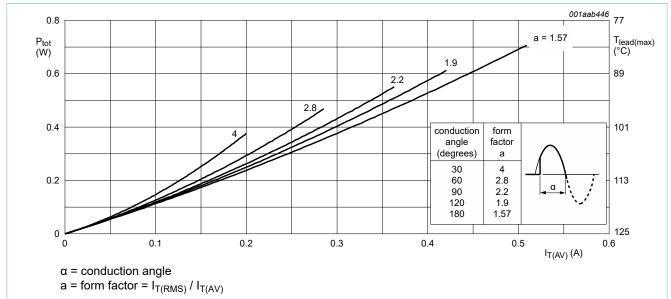


Fig. 1. Total power dissipation as a function of average on-state current; maximum values

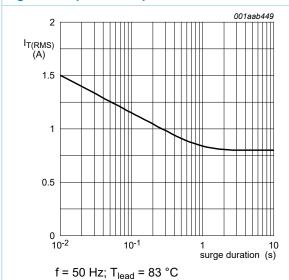


Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents

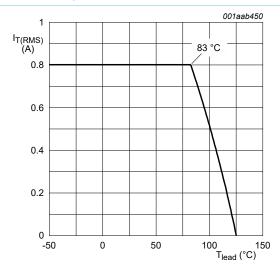


Fig. 3. RMS on-state current as a function of lead temperature; maximum values

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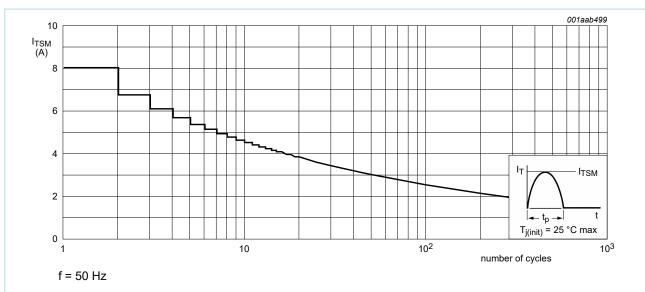


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

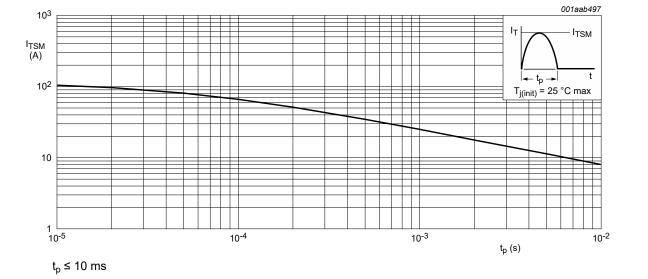


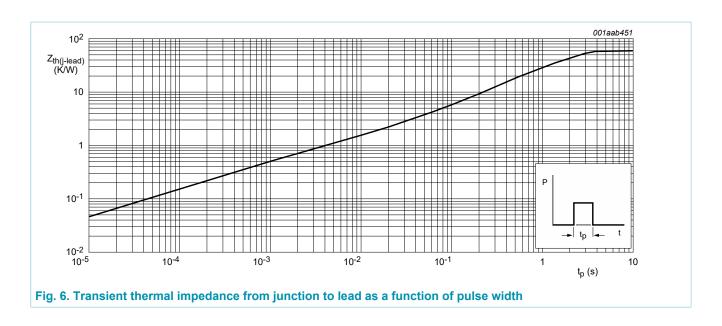
Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	<u>Fig. 6</u>	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,	,		
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 7	-	50	200	μA
lL	latching current	V_D = 12 V; I_G = 0.5 mA; T_j = 25 °C; Fig. 8	-	2	6	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	2	5	mA
V _T	on-state voltage	I _T = 1.2 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.25	1.7	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 11	-	0.5	0.8	V
		$V_D = 400 \text{ V}; I_T = 10 \text{ mA}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.2	0.3	-	V
I _D	off-state current	V _D = 400 V; T _j = 125 °C	-	0.05	0.1	mA
I _R	reverse current	V _R = 400 V; T _j = 125 °C	-	0.05	0.1	mA
Dynamic cl	naracteristics			,		
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 268 V; T_j = 125 °C; R_{GK} = 1 kΩ; exponential waveform; Fig. 12	500	800	-	V/µs
		V _{DM} = 268 V; T _j = 125 °C; exponential waveform; gate open circuit; Fig. 12	-	25	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 2 A; V_D = 400 V; I_G = 10 mA; $dI_G/$ dt = 0.1 A/µs; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 268 V; T_j = 125 °C; I_{TM} = 1.6 A; V_R = 35 V; $(dI_T/dt)_M$ = 30 A/µs; dV_D/dt = 2 V/µs; $R_{GK(ext)}$ = 1 k Ω	-	100	-	μs

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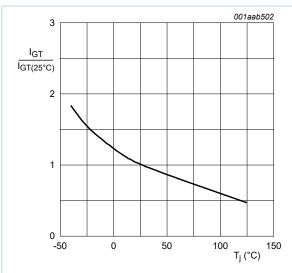


Fig. 7. Normalized gate trigger current as a function of junction temperature

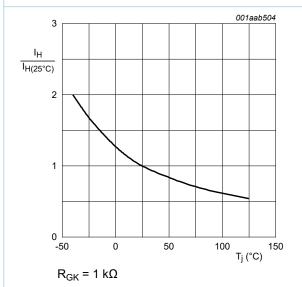


Fig. 9. Normalized holding current as a function of junction temperature

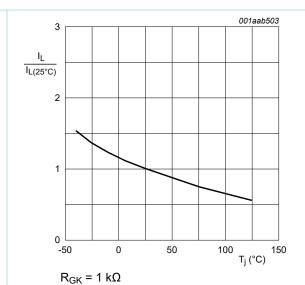
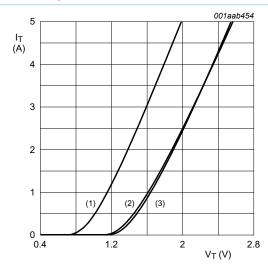


Fig. 8. Normalized latching current as a function of junction temperature



 V_o = 1.067 V; R_s = 0.187 Ω

(1) T_i = 125 °C; typical values

(2) T_j = 125 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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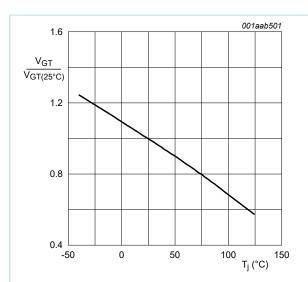


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

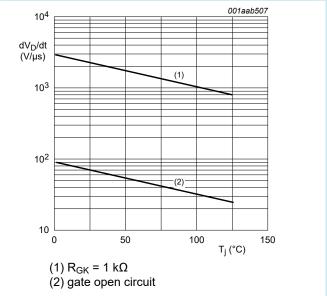
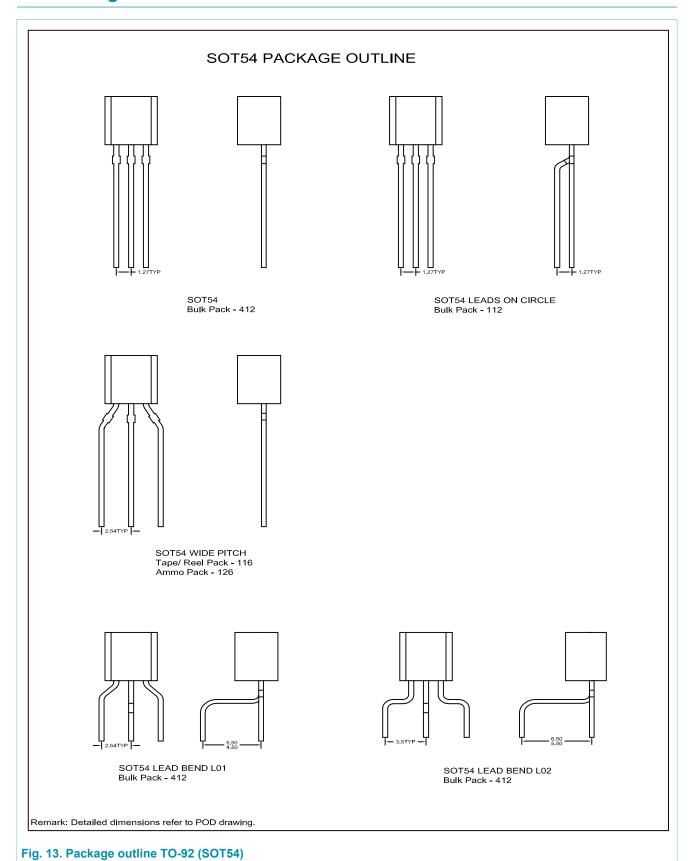


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

11. Package outline



Product data sheet

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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